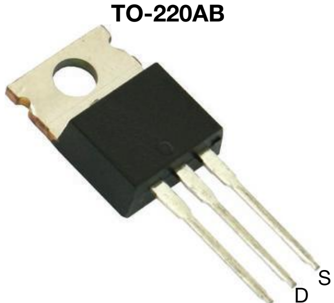
LB3036G-VB Datasheet
N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0016
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0020
I_D (A)	270
Configuration	Single

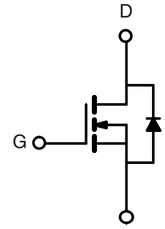
FEATURES
- Trench power MOSFET
- Package with low thermal resistance
- 100 % R_g and UIS tested

RoHS COMPLIANT
HALOGEN FREE

TO-220AB



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	T_C = 25 °C	I_D	270	A
	T_C = 125 °C		120 [a]	
Continuous Source Current (Diode Conduction)		I_S	120 [a]	
Pulsed Drain Current [b]		I_{DM}	600	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	75	
Single Pulse Avalanche Energy		E_{AS}	281	mJ
Maximum Power Dissipation [b]	T_C = 25 °C	P_D	375	W
	T_C = 125 °C		125	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount [c]	R_{thJA}	40	°C/W
Junction-to-Case (Drain)		R_{thJC}	0.4	

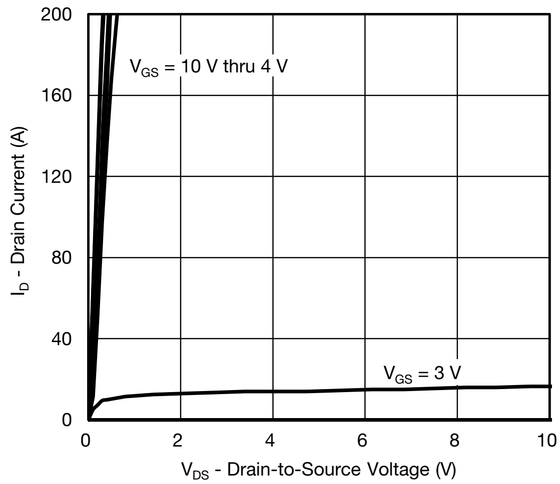
Notes
a. Package limited.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
c. When mounted on 1" square PCB (FR4 material).

SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA		60	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA		1.5	2.0	2.5	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 60 V	-	-	1	μA
		V_{GS} = 0 V	V_{DS} = 60 V, T_J = 125 °C	-	-	50	μA
		V_{GS} = 0 V	V_{DS} = 60 V, T_J = 175 °C	-	-	1.5	mA
On-State Drain Current [a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ≥ 5 V	120	-	-	A
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 30 A	-	0.0016	-	Ω
		V_{GS} = 10 V	I_D = 30 A, T_J = 125 °C	-	0.0031	-	Ω
		V_{GS} = 10 V	I_D = 30 A, T_J = 175 °C	-	0.0037	-	Ω
		V_{GS} = 4.5 V	I_D = 20 A	-	0.0020	-	Ω
Forward Transconductance [b]	g_{fs}	V_{DS} = 15 V, I_D = 30 A		-	164	-	S
Dynamic [b]							
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	-	12 060	15 100	pF
Output Capacitance	C_{oss}			-	5750	7200	pF
Reverse Transfer Capacitance	C_{rss}			-	860	1100	pF
Total Gate Charge [c]	Q_g	V_{GS} = 10 V	V_{DS} = 30 V, I_D = 80 A	-	128	200	nC
Gate-Source Charge [c]	Q_{gs}			-	33	-	nC
Gate-Drain Charge [c]	Q_{gd}			-	11	-	nC
Gate Resistance	R_g	f = 1 MHz		0.8	1.68	2.6	Ω
Turn-On Delay Time [c]	$t_{d(on)}$	V_{DD} = 30 V, R_L = 0.375 Ω I_D ≅ 80 A, V_{GEN} = 10 V, R_g = 1 Ω		-	20	25	ns
Rise Time [c]	t_r			-	15	40	ns
Turn-Off Delay Time [c]	$t_{d(off)}$			-	65	100	ns
Fall Time [c]	t_f			-	12	20	ns
Source-Drain Diode Ratings and Characteristics [b]							
Pulsed Current [a]	I_{SM}			-	-	300	A
Forward Voltage	V_{SD}	I_F = 80 A, V_{GS} = 0 V		-	0.88	1.5	V

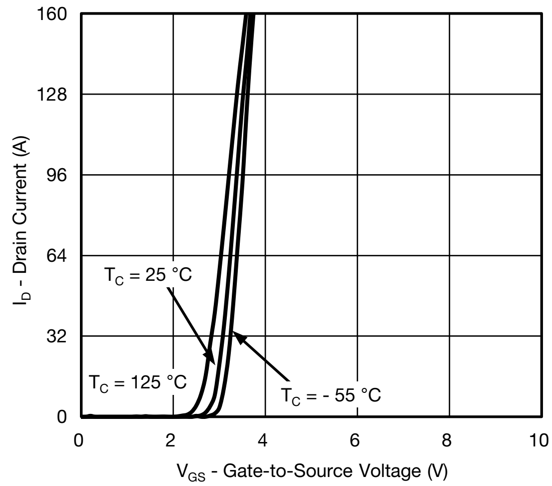
Notes

a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

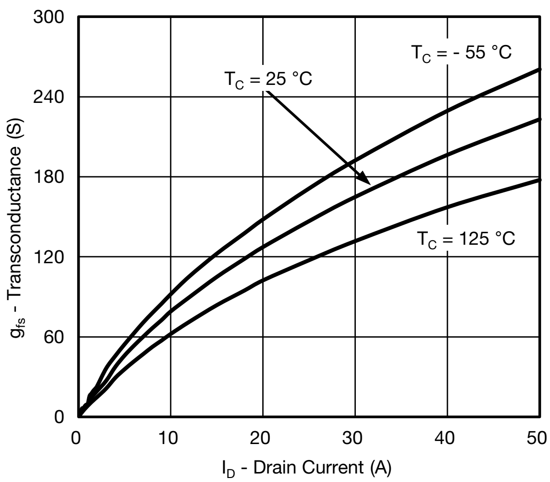
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



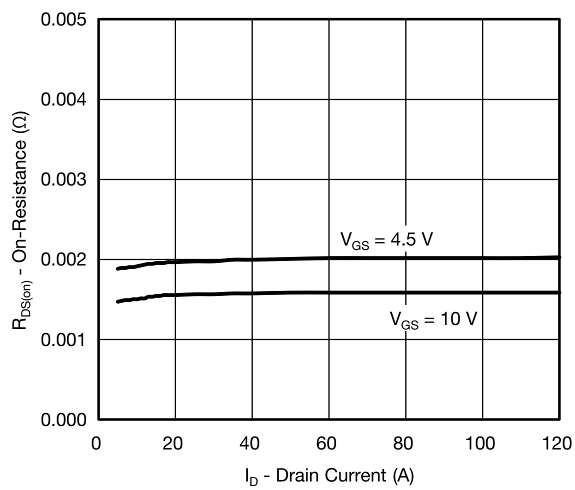
Output Characteristics



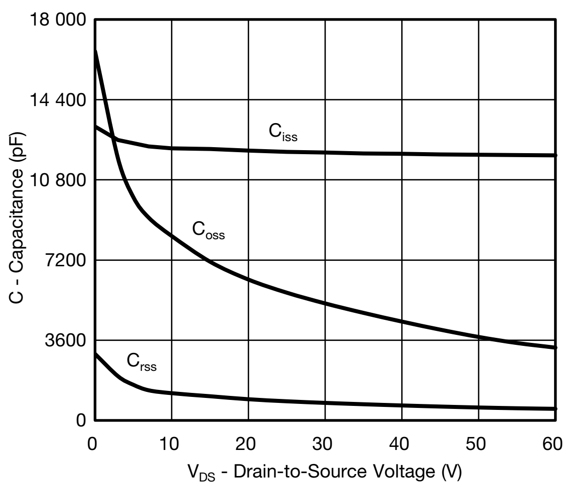
Transfer Characteristics



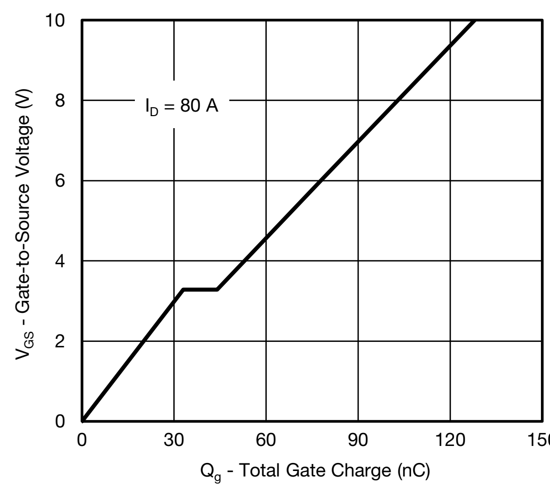
Transconductance



On-Resistance vs. Drain Current

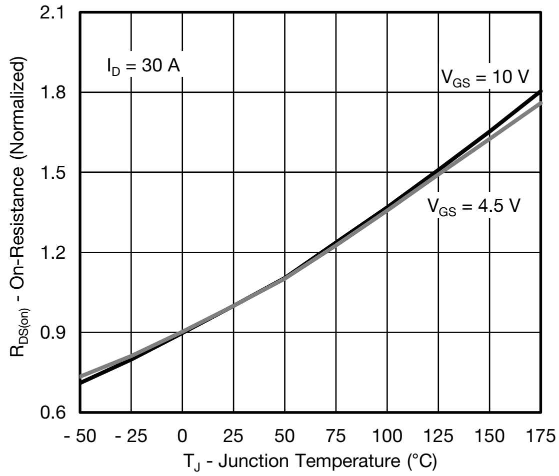


Capacitance

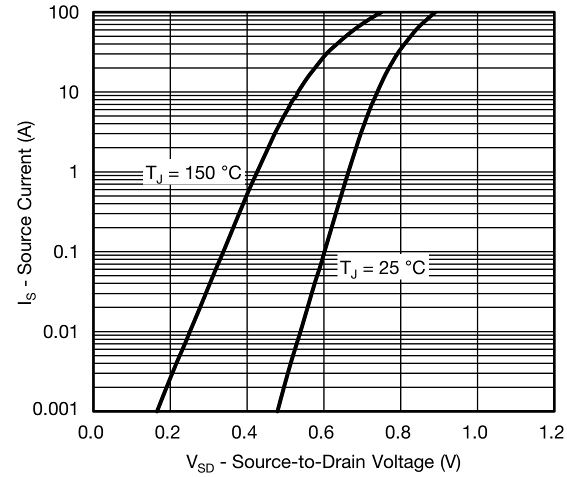


Gate Charge

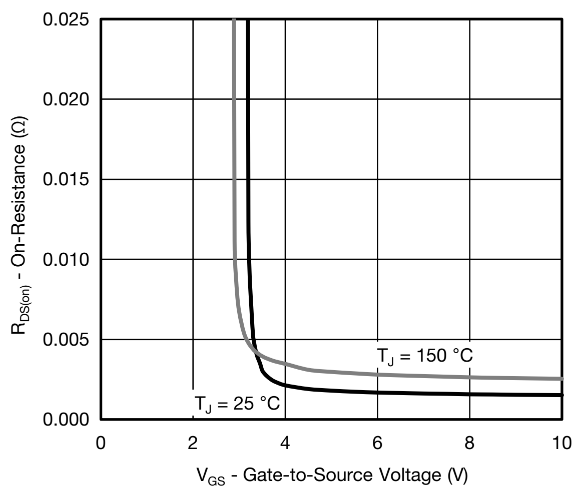
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



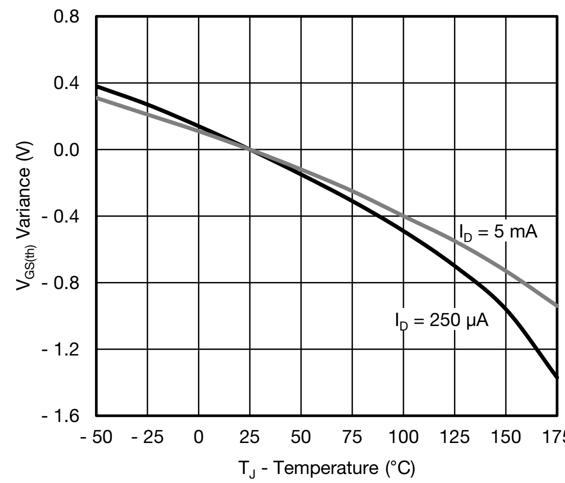
On-Resistance vs. Junction Temperature



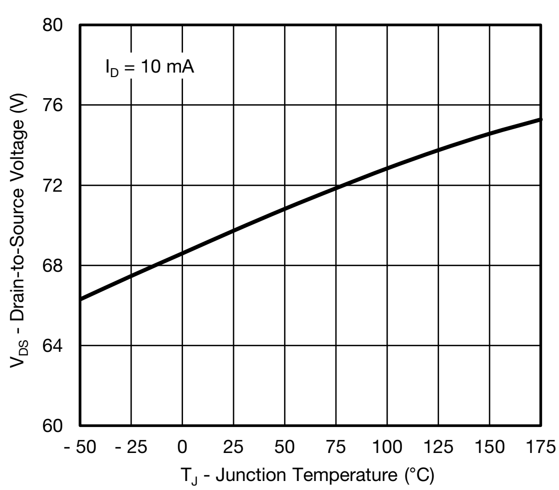
Source Drain Diode Forward Voltage



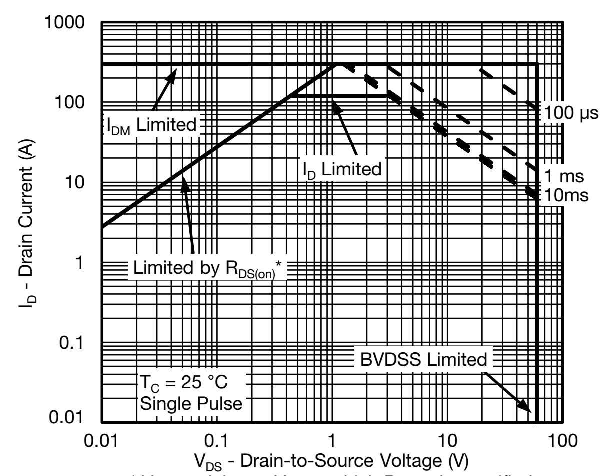
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



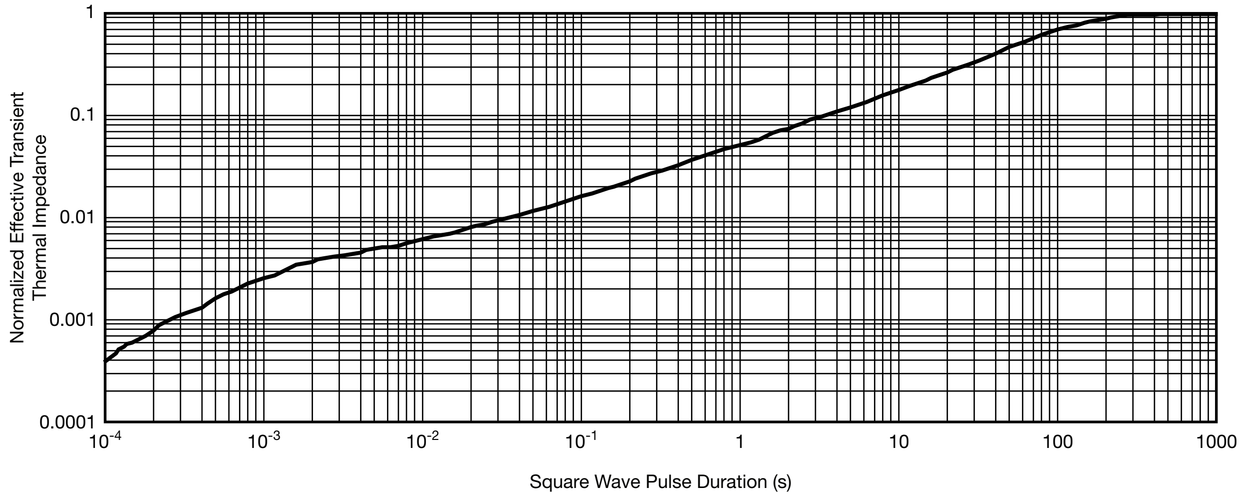
Drain Source Breakdown vs. Junction Temperature



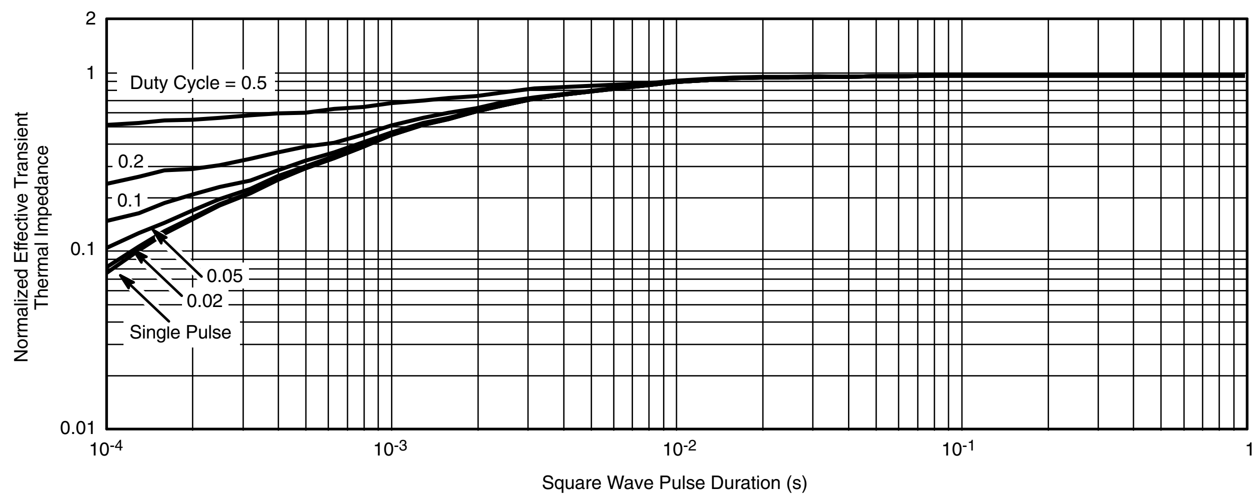
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



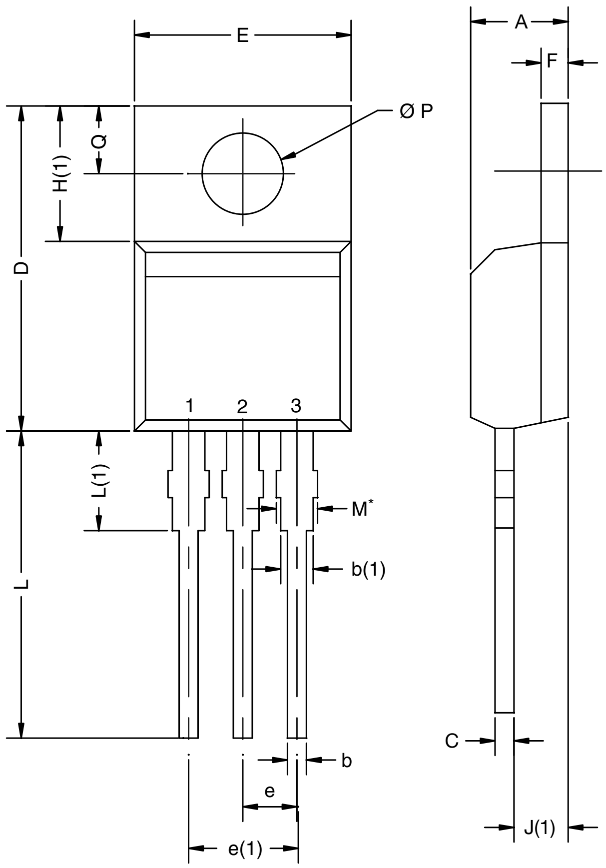
Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

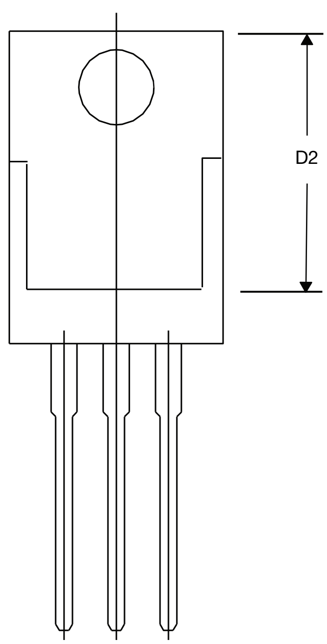
  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-220AB



DIM.		INCHES MIN.	INCHES MAX.	MILLIMETERS MIN.	MILLIMETERS MAX.
A		0.160	0.190	4.064	4.826
b		0.020	0.039	0.508	0.990
b1		0.020	0.035	0.508	0.889
b2		0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2		0.045	0.055	1.143	1.397
D		0.340	0.380	8.636	9.652
D1		0.220	0.240	5.588	6.096
D2		0.038	0.042	0.965	1.067
D3		0.045	0.055	1.143	1.397
D4		0.044	0.052	1.118	1.321
E		0.380	0.410	9.652	10.414
E1		0.245	-	6.223	-
E2		0.355	0.375	9.017	9.525
E3		0.072	0.078	1.829	1.981
e		0.100 BSC		2.54 BSC	
K		0.045	0.055	1.143	1.397
L		0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
L2		0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
L4		0.010 BSC		0.254 BSC	
M		-	0.002	-	0.050

ECN: T13-0707-Rev. K, 30-Sep-13
DWG: 5843



Notes

1. Plane B includes maximum features of heat sink tab and plastic.
2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
3. Pin-to-pin coplanarity max. 4 mils.
4. *: Thin lead is for SUB, SYB.
   Thick lead is for SUM, SYM, SQM.
5. Use inches as the primary measurement.
6. This feature is for thick lead.

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